

〔電気システム工学〕

29-28 Nitrogen Ion Surface Modification of Flash Evaporated InP

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Flash evaporated InP shows good crystal quality for solar cells, after nitrogen ion -beam modification. The ion implantation is effective to (1) reduction of defects and (2) alternation of conduction type to p-type. The procedure of the ion modification is expected as a simple and reliable process to develop InP for space solar cells.

(Solar Energy Materials and Solar Celles (1996))